Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)}	15 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.1 V							
t _{rr}	29 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching
 HALOGEN
 FREE
 losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V _{RRM}		1200	V					
Average rectified forward current	I _{F(AV)}	T _C = 98 °C, D = 0.50	15						
Repetitive peak forward current	I _{FRM}	T _C = 98 °C, D = 0.50, f = 20 kHz	30	A					
Non-repetitive peak surge current	I _{FSM}	T_{C} = 45 °C, t_{p} = 10 ms, sine wave	110						
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-				
	VF	I _F = 15 A	-	2.5	3.3	V			
Forward voltage	VF	I _F = 15 A, T _J = 125 °C	-	2.1	-				
Deveree leekere eurrent	1	V _R = V _R rated	-	-	50				
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V _R = 200 V	-	10	-	pF			
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH			

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Document Number: 96812

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COMPLIANT







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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)											
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1.0 \text{ A}, dI_F/c$	$t = 100 \text{ A/}\mu\text{s}, \text{V}_{\text{R}} = 30 \text{ V}$	-	29	-					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	96	-	ns				
		T _J = 125 °C		-	137	-					
Peak recovery current	1	T _J = 25 °C	l _F = 10 A dl _F /dt = 600 A/µs	-	11.5	-	A nC				
	I _{RRM}	T _J = 125 °C	αι _F /ατ = 600 Α/μs V _R = 400 V	-	16	-					
Reverse recovery charge	0	T _J = 25 °C		-	375	-					
neverse recovery charge	Q _{rr}	T _J = 125 °C		-	900	-	no				
Reverse recovery time	+	T _J = 25 °C		-	77.5	-	20				
nevelse recovery line	t _{rr}	T _J = 125 °C		-	106	-	ns				
Peak recovery current	1	T _J = 25 °C	l _F = 15 A dl _F /dt = 1000 A/µs	-	21	-	А				
Feak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 800 {\rm V}$	-	29	-	A				
	0	T _J = 25 °C		-	680	-	nC				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1600	-	nc				

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7	°C/W					
Weight			-	2.0	-	g					
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)					
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C					
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	E5TX1512SH								

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VS-E5TX1512S2LHM3

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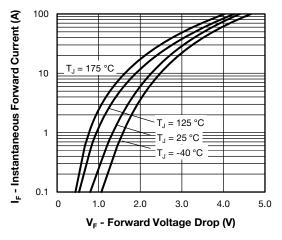


Fig. 1 - Forward Voltage Drop Characteristics

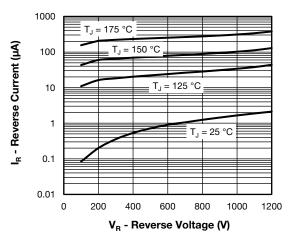


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

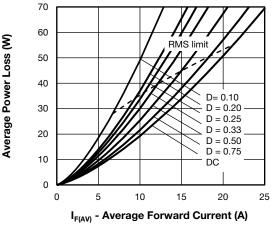


Fig. 5 - Forward Power Loss Characteristics

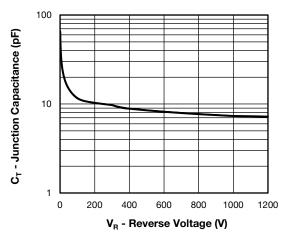


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

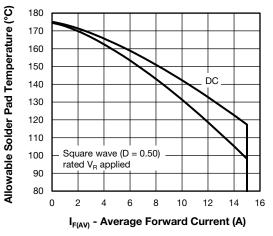


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

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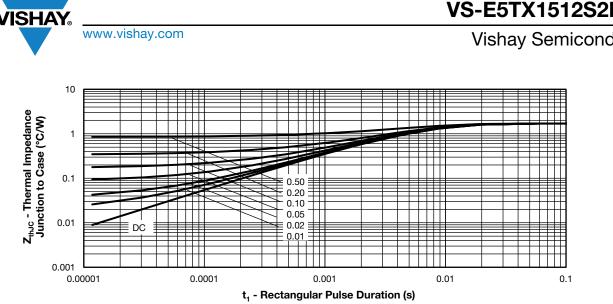
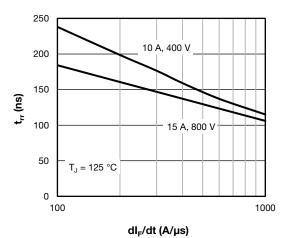


Fig. 6 - Transient Thermal Impedance, Junction to Case





1800 1600 15 A, 800 V 1400 1200 10 A, 400 V С ц 1000 ď 800 600 400 T_{.1} = 125 °C 200 0 100 1000 dl_F/dt (A/µs)

Fig. 8 - Typical Stored Charge vs. dl_F/dt

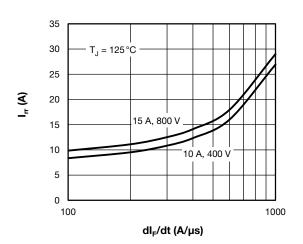


Fig. 9 - Typical Recovery Current vs. dI_F/dt

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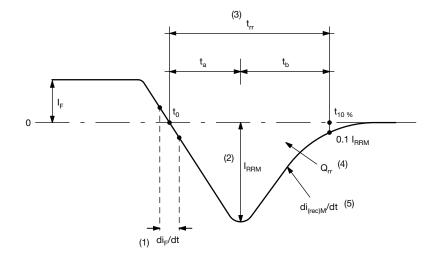


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- ⁽¹⁾ di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}~di_{(rec)}M/dt$ - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	Е	5	т	x	15	12	S2	L	н	МЗ
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)	(11)
		· Visł	\bigcirc	nicondu	Ŭ	Ŭ	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc
	2 - E = single diode										
	3 - 5 = FRED generation 5										
	4 - Package:										
				2L (TO-		packag	ge				
	5 -	• X =	hyperfa	st recov	/ery						
	6 -	· Cur	rent rati	ng (15 =	= 15 A)						
	7 -	· Volt	tage rati	ng (12 =	= 1200 \	/)					
	8	- S2	= true 2	pin D ² F	PAK						
	 9 - None = tube (50 pieces) • L = tape and reel (left oriented, for D²PAK package) 										
	If needed different orientation/packaging, please contact factory										
	10 - H = AEC-Q101 qualified										
	 H = AEC-Q101 qualified Environmental digit: M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free 										

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-E5TX1512S2LHM3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						

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		www.vishay.com

VS-E5TX1512S2LHM3

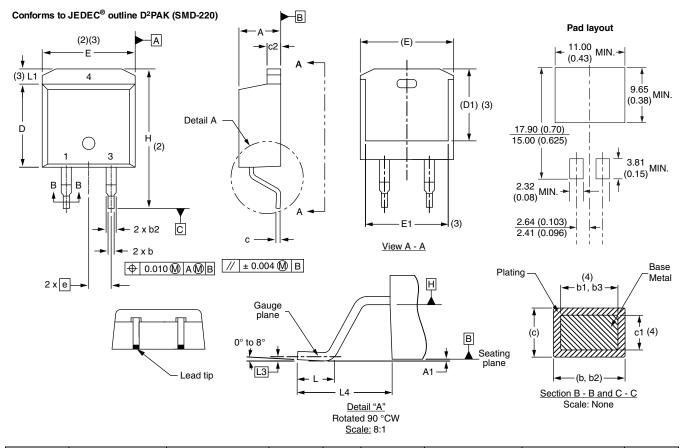
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D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3	
A1	0.00	0.254	0.000	0.010		Е	9.65	10.67	0.380	0.420	2, 3	
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3	
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC			
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625		
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110		
с	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3	
c1	0.38	0.58	0.015	0.023	4	L3	0.25 BSC		L3 0.25 BSC 0.010 BSC		BSC	
c2	1.14	1.65	0.045	0.065		L4	4.78	5.28	0.188	0.208		
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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